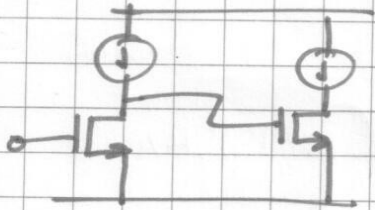


16 AUG 2019

 $f_T$  discussionTransition frequency -

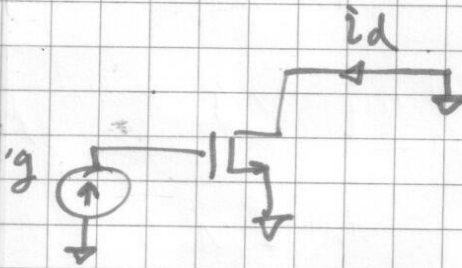
voltage gain = 1

$$\omega_T = \frac{g_m}{C_{gs}}$$

Current gain = 1

$$\omega_T = \frac{g_m}{C_{gs}}$$

Give an idea  
of raw speed  
capability of  
transistor



Why Transit frequency?

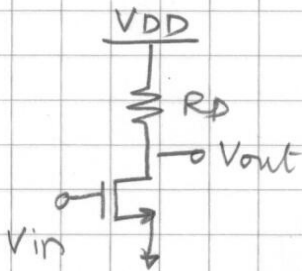
$$\omega_T \frac{f_T}{\cancel{f_T}} = \frac{g_m}{C_{gs}} = \frac{\mu_n \epsilon_{ox} \frac{W}{L} (V_{GS} - V_{TH})}{\frac{2}{3} \epsilon_{ox} W \cdot L} = \frac{\left[ \frac{3}{2} \frac{(V_{GS} - V_{TH})}{L} \right] \mu_n}{L}$$

$$= \frac{\mu_n [E_{channel}]}{L} = \frac{v}{L} = \frac{1}{\tau_T}$$

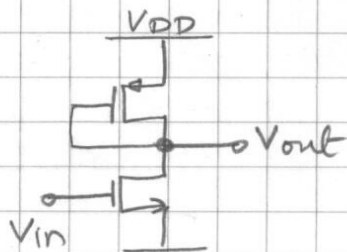
Transit Time  
from source to drain

$f_T \Rightarrow$  gives an idea of intrinsic delay of device.

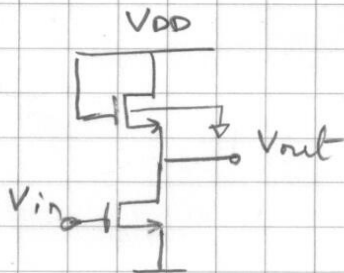
Recap  $f_T$  discussion. — Why Transit frequency



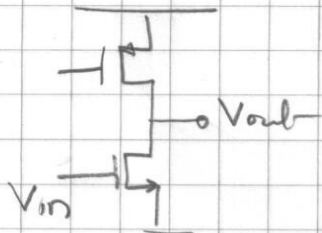
$$\frac{V_{out}}{V_{in}} \approx -g_m (r_o \parallel R_D)$$



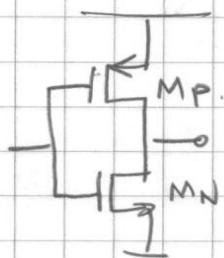
$$\frac{V_{out}}{V_{in}} \approx -\frac{g_{m1}}{g_{m2}}$$



$$\frac{V_{out}}{V_{in}} = -\frac{g_{m1}}{g_{m2} + g_{mbs2}}$$

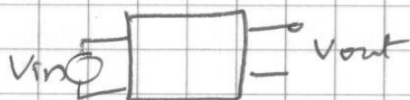


$$\frac{V_{out}}{V_{in}} = -g_{m1} (r_{o1} \parallel r_{o2})$$



$$\frac{V_{out}}{V_{in}} = -\frac{(g_{mN} + g_{mP})}{(g_{dsN} + g_{dsP})}$$

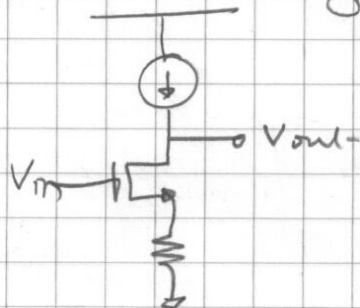
## XF Theorem



Short Ckt  $g_m$  &  $R_{out}$

$$\frac{V_{out}}{V_{in}} = -g_m R_{out}$$

## Source degeneration

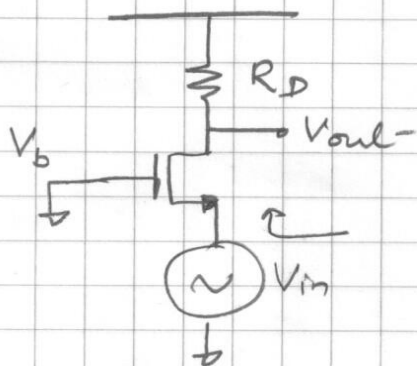


$$G_m \approx \frac{g_m}{1 + g_m R_s}$$

$$R_{out} = g_m r_o R_s + r_o$$

$$\frac{V_{out}}{V_{in}} \approx -G_m R_{out} = -g_m r_o$$

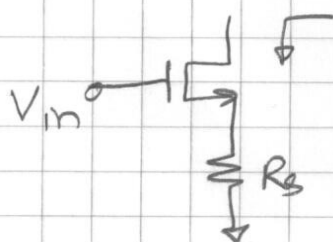
## Common Gate Amplifier



$$\frac{V_{out}}{V_{in}} = \frac{g_m r_o}{(r_o + R_D)} R_D$$

(Body effect ignored)

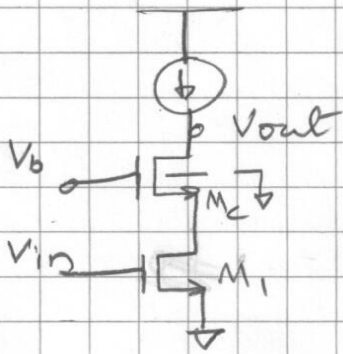
$$Z_{in} = \frac{r_o + R_D}{(g_m r_o + 1)} \approx \frac{r_o + R_D}{(g_m r_o)} \approx \frac{1}{g_m} \quad (R_D \gg r_o)$$



$$R_{out} = (g_m r_o) R_s + r_o$$

$$R_{out} \uparrow (g_m r_o) \text{ factor}$$

## Cascode Common Source Amplifier



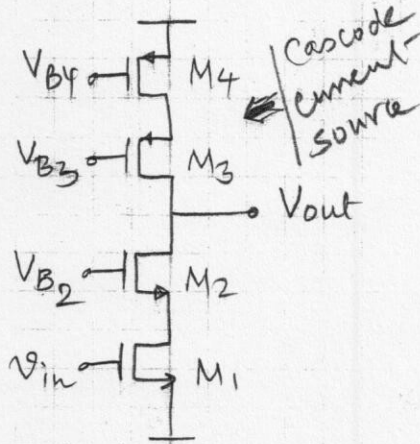
$$A_v = -G_m R_{out}$$

$$\approx -g_{m1} (g_{m2} r_{oc} \cdot r_{o1})$$

$$\approx -(g_{m1} r_{o1}) (g_{m2} r_{oc})$$



# Cascode Stage with current source



$$G_m = g_{m1}$$

$$R_{out} = (g_{m2} r_{o2}) r_{o1} \parallel (g_{m3} r_{o3}) r_{o4}$$

Assuming  $r_{o1} = r_{o2} = r_{o3} = r_{o4} = r_o$

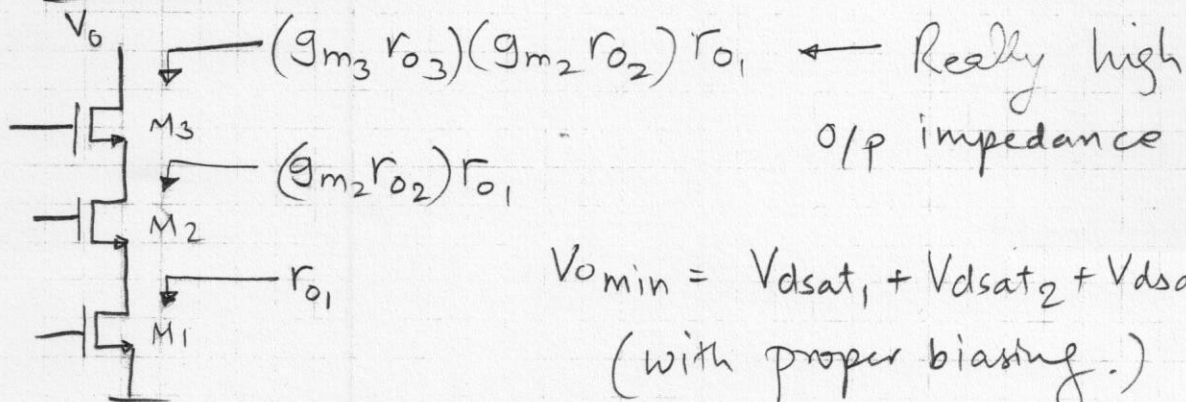
$$g_{m1} = g_{m2} = g_{m3} = g_{m4} = g_m$$

$$A_v = -\frac{1}{2} (g_m r_o)^2$$

$$V_{out\ min} = V_{dsat1} + V_{dsat2}$$

$$V_{out\ max} = V_{dd} - (|V_{dsat3}| + |V_{dsat4}|)$$

## Tripple Cascode



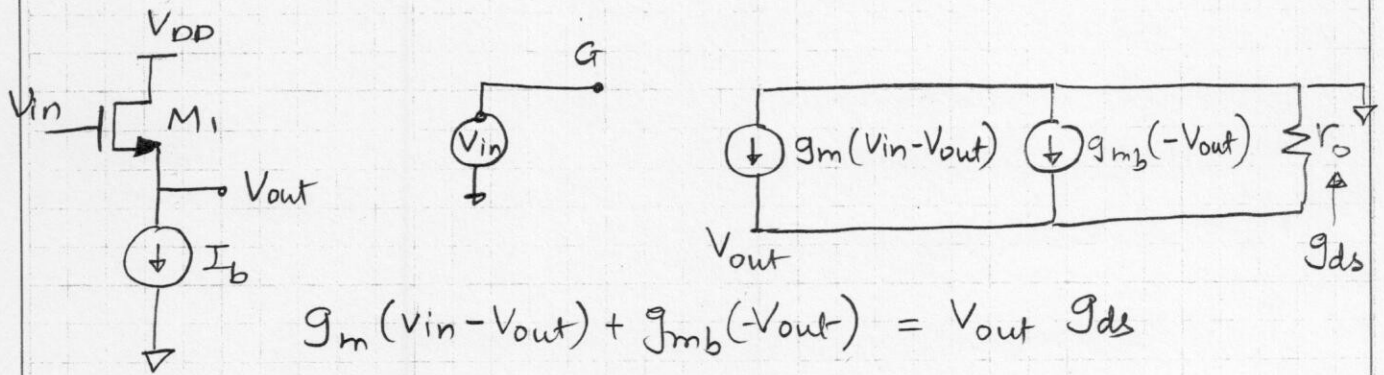
$$V_{o\ min} = V_{dsat1} + V_{dsat2} + V_{dsat3}$$

(with proper biasing.)

Also called

## Telescopic Cascode

## Common drain Amplifier (Source follower)



$$g_m(V_{in} - V_{out}) + g_{mb}(-V_{out}) = V_{out} g_{ds}$$

$$(g_m + g_{mb} + g_{ds}) V_{out} = g_m V_{in}$$

$$\frac{V_{out}}{V_{in}} = \frac{g_m}{g_m + g_{mb} + g_{ds}} \approx \frac{g_m}{g_m + g_{mb}} = \frac{1}{1 + \eta} \approx 1$$

→ Non-inverting unity gain. amplifier

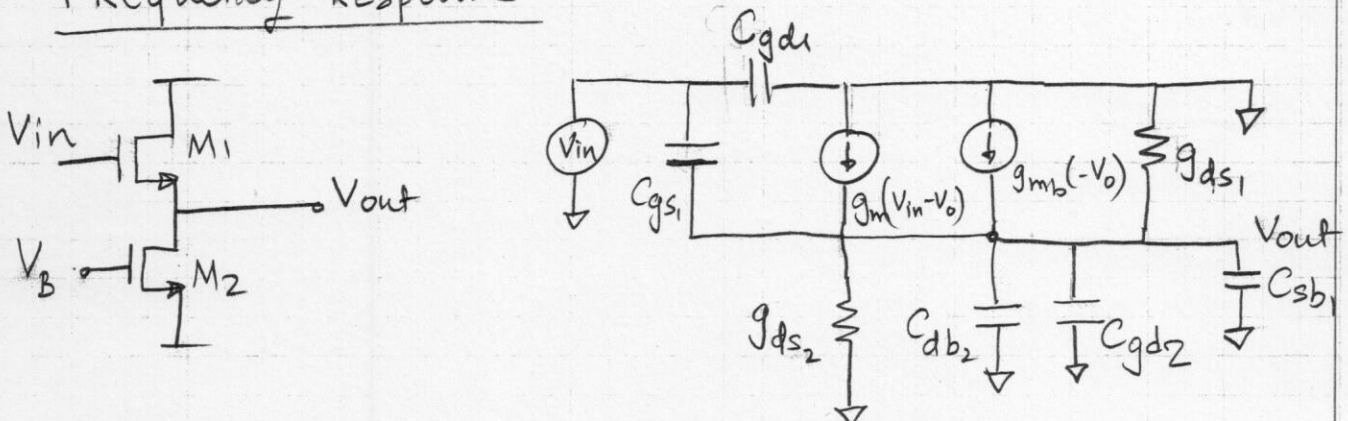
$$r_{in} = \infty \quad r_{out} = \frac{1}{g_m + g_{mb} + g_{ds}} \approx \frac{1}{g_m} \text{ Low imp.}$$

→ O/P DC range

$$V_{out} = V_{in} - (V_{T1} + V_{dsat1})$$

$$\begin{aligned} V_{out\max} &= V_{DD} - (V_T + V_{dsat}) \\ V_{in\max} &= V_{DD} \\ V_{in\min} &= V_T + V_{dsat} + V_{dsat} \end{aligned}$$

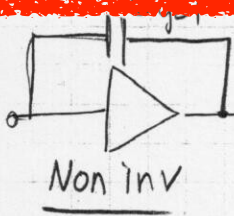
→ DC-level shifter & Buffer. (low o/p imp) <sub>cs</sub>

Frequency Response

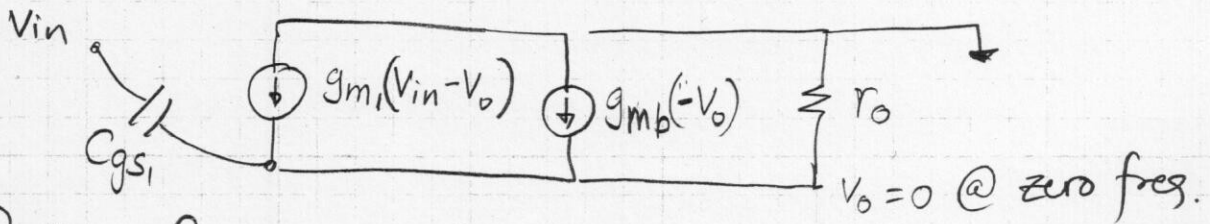
$$A_v = \text{DC gain} \cdot \frac{(1 - \frac{s}{\omega_z})}{(1 - \frac{s}{\omega_p})}$$



LHP  $\omega_p = -\frac{g_{out}}{C_{out}} = -\frac{g_{m1} + g_{mbs1} + g_{ds1} + g_{ds2}}{C_{gs1} + C_{sb1} + C_{db2} + C_{gd2}}$



$\Rightarrow$  LHP zero.

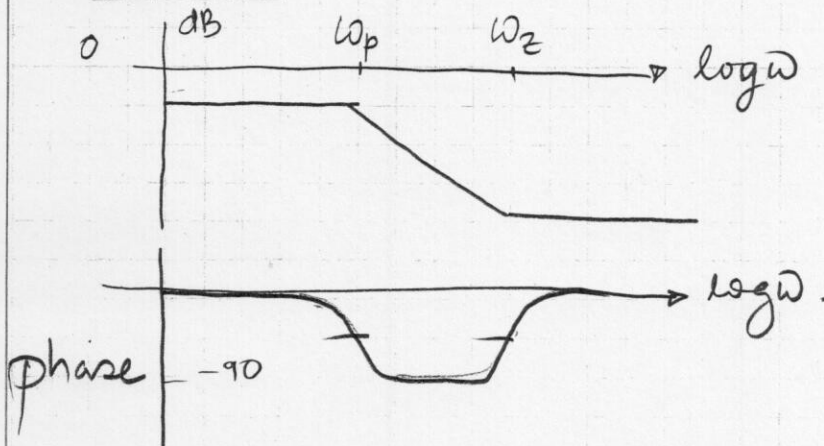


@ Zero frequency  $\omega_z$

$$\omega_z C_{gs1} \cdot V_{in} = -g_{m1} V_{in} \Rightarrow \boxed{\omega_z = -\frac{g_{m1}}{C_{gs1}}}$$

$$A_v = \frac{g_{m1}}{g_{m1} + g_{mbs1} + g_{ds1} + g_{ds2}} \cdot \frac{\left(1 + \frac{s}{g_{m1}/C_{gs1}}\right)}{\left(1 + \frac{s}{\frac{g_{m1} + g_{mbs1} + g_{ds1} + g_{ds2}}{C_{gs1} + C_{sb1} + C_{db2} + C_{gd2}}}\right)}$$

Bode Plot



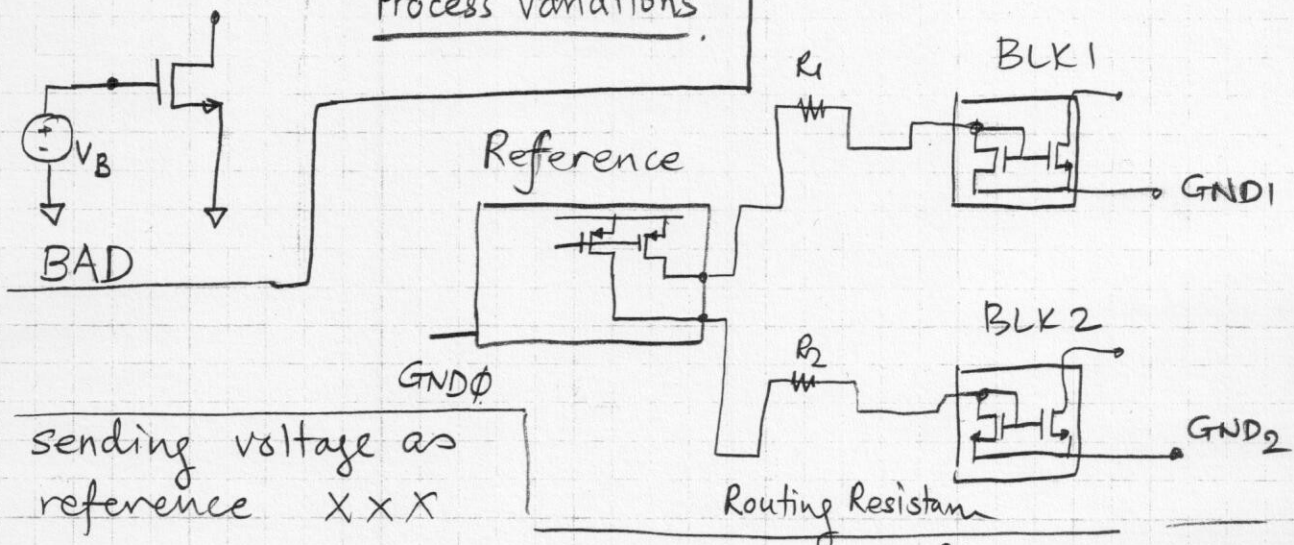
# New Topic MOS Current Mirrors/Sources

Novice Biasing

Process variations

ON CHIP

CURRENT DISTRIBUTION



- Gnd/Vdd potentials could be different
- transistor properties across the chip change.

Current Sources used for DC biasing,  
Active load to get max gain without IR drop.

- Specs
- Output Resistance
  - voltage compliance (min or max voltage)
  - Accuracy & process independance.
  - DC balance (for mirror)
  - I/p Resistance (for mirror)